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Invention: 4

COMPOSITION FOR ANTIREFLECTIVE COATING AND METHOD FOR FORMING SAME

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(21)Application number : 58-146398 (71)Applicant : HITACHI LTD

(22)Date of filing : 12.08.1983 (72)Inventor : TANAKA TOSHIHIKO

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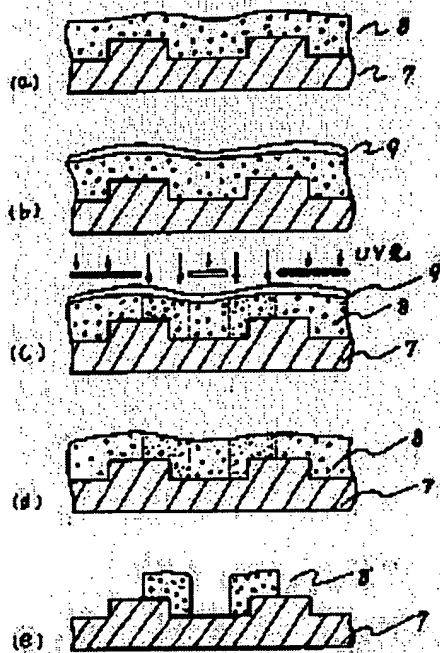
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(54) PATTERN FORMING METHOD

(57)Abstract:

PURPOSE: To enable to form a microscopic and highly accurate pattern by a method wherein a light transmitting type reflection preventing film is formed on a photoresist film and an exposure is performed thereon.

CONSTITUTION: A photoresist 8 is formed on an Si substrate 7 having a stepping by performing an ordinary method, and then a polysiloxin film 9 is formed by application as a reflection preventing film on the photoresist 8. The absorption coefficient of the polysiloxin is to be  $10^{-2}$  or below in the wavelength 436nm of the exposure light, and the light can be passed through completely. Subsequently, an ordinary exposure is performed using the light of wavelength 436nm. Then, the polysiloxin 9 is removed using xylene, and a photoresist 8' is formed on the Si substrate by performing an ordinary developing process. The reflection preventing film is not limited to polysiloxin only, and any material such as polyvinyl alcohol and the like, which reduces reflection based on the principle of reflection prevention and which passes through the exposure light completely and which gives no degeneration on the photoresist, can be used.



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